Triacs Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 800 V
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Three Modes (MAC15 Series) or Four Modes (MAC15A Series)
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|---------------------------------------|-------------------|------------------|
| $\begin{array}{l} \mbox{Peak Repetitive Off-State Voltage Note 1} \\ (T_J = -40 \ to \ +125^\circ C, \ Sine \ Wave 50 \ to \ 60 \ Hz, \\ Gate \ Open) & MAC15A6G \\ MAC15-8G, \ MAC15A8G \\ MAC15-10G, \ MAC15A10G \end{array}$ | V _{DRM,} V _{RRM} | 400 600 800 | > |
| Peak Gate Voltage (Pulse Width $\leq 1.0 \ \mu sec; T_C = 90^{\circ}C$) | V _{GM} | 10 | V |
| On-State Current RMS; Full Cycle Sine Wave 50 to 60 Hz (T_C = +90°C) | I _{T(RMS)} | 15 | A |
| Circuit Fusing Consideration (t = 8.3 ms) | l ² t | 93 | A ² s |
| Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = +80^{\circ}C$) Preceded and Followed by Rated Current | I _{TSM} | 150 | A |
| Peak Gate Power (T _C = +80°C, Pulse Width = 1.0 μs) | P _{GM} | 20 | W |
| Average Gate Power (T_C = +80°C, t = 8.3 ms) | P _{G(AV)} | 0.5 | W |
| Peak Gate Current (Pulse Width $\leq 1.0 \ \mu sec; T_C = 90^{\circ}C$) | I _{GM} | 2.0 | A |
| Operating Junction Temperature Range | TJ | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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TRIACS **15 AMPERES RMS** 400 thru 800 VOLTS







- = Year
- ww = Work Week
- G = Pb-Free Package

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

| PIN ASSIGNMENT | | | |
|----------------|-----------------|--|--|
| 1 | Main Terminal 1 | | |
| 2 | Main Terminal 2 | | |
| 3 | Gate | | |
| 4 | Main Terminal 2 | | |

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

THERMAL CHARACTERISTICS

| Characteristic | | Value | Unit |
|---|----|-------|------|
| Thermal Resistance, Junction-to-Case | | 2.0 | °C/W |
| Thermal Resistance, Junction-to-Ambient | | 62.5 | °C/W |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds | ΤL | 260 | °C |

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

| Characteristic | | Min | Тур | Max | Unit |
|--|-----------------|------------|--------------------------|----------------------|----------|
| DFF CHARACTERISTICS | | | • | • | • |
| $ \begin{array}{ll} \mbox{Peak Blocking Current} & T_J = 25^{\circ} \\ \mbox{(V}_D = \mbox{Rated V}_{DRM}, \mbox{V}_{RRM}; \mbox{Gate Open)} & T_J = 125^{\circ} \end{array} $ | | | - | 10 2.0 | μA mA |
| ON CHARACTERISTICS | | | | | |
| Peak On-State Voltage Note 2 (I _{TM} = ±21 A Peak) | V _{TM} | - | 1.3 | 1.6 | V |
| Gate Trigger Current (Continuous dc) (V_D = 12 Vdc, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY | I _{GT} | | - - - - | 50 50 50 75 | mA |
| Gate Trigger Voltage (Continuous dc) (V_D = 12 Vdc, R_L = 100 Ω) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+) "A" SUFFIX ONLY | V _{GT} | | 0.9 0.9 1.1 1.4 | 2 2 2 2.5 | V |
| Gate Non–Trigger Voltage (V _D = 12 V, R _L = 100 Ω) T _J = 110°C) MT2(+), G(+); MT2(-), G(-); MT2(+), G(-) MT2(-), G(+) "A" SUFFIX ONLY | | 0.2 0.2 | | | V |
| Holding Current (V_D = 12 Vdc, Gate Open, Initiating Current = ±200 mA) | | - | 6.0 | 40 | mA |
| Turn-On Time (V _D = Rated V _{DRM} , I _{TM} = 17 A) (I _{GT} = 120 mA, Rise Time = 0.1 μ s, Pulse Width = 2 μ s) | | - | 1.5 | - | μs |
| DYNAMIC CHARACTERISTICS | | | • | | |
| Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM} , I_{TM} = 21 A, Commutating di/dt = 7.6 A/ms, Gate Unenergized, T_C = 80°C) | | - | 5.0 | - | V/μs |

2. Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

ORDERING INFORMATION

| Device | Device Marking | Package | Shipping |
|-----------|----------------|-----------------------|----------------|
| MAC15-8G | MAC15-8 | TO-220AB (Pb-Free) | |
| MAC15-10G | MAC1510 | TO-220AB (Pb-Free) | |
| MAC15A6G | MAC15A6 | TO-220AB (Pb-Free) | 500 Units Bulk |
| MAC15A8G | MAC15A8 | TO-220AB (Pb-Free) | |
| MAC15A10G | MAC15A10 | TO-220AB (Pb-Free) | |

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Parameter | |
|---|--|
| Peak Repetitive Forward Off State Voltage | |
| Peak Forward Blocking Current | |
| Peak Repetitive Reverse Off State Voltage | |
| Peak Reverse Blocking Current | |
| Maximum On State Voltage | |
| Holding Current | |
| | |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.



Figure 3. Typical Gate Trigger Voltage

Figure 4. Typical Gate Trigger Current



Figure 8. Thermal Response

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 **ISSUE AG**



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